

KEL55L

The KEL55L is a high - power GaAs IRED mounted in a clear plastic package. This LED emits infrared light through two plastic lenses on both sides of the package is ideally suited for use with VTR tape - end sensors.

FEATURES

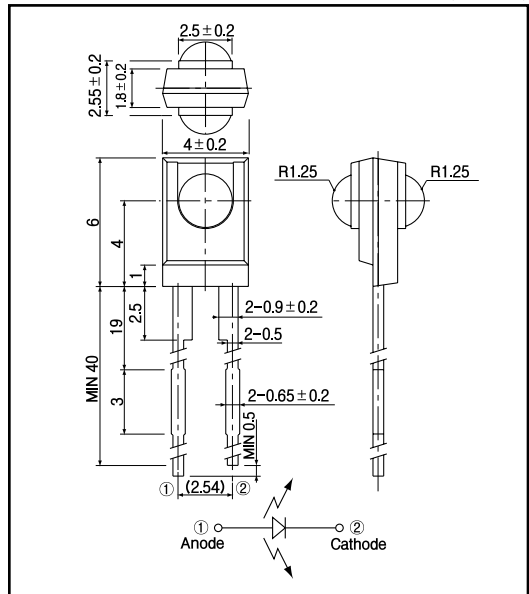
- Compact
- Low profile package
- Low - cost
- Sidelooking plastic package
- Long - lead type

APPLICATIONS

- VTR type - end sensor

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

($T_a = 25^\circ\text{C}$)

Item	Symbol	Rating	Unit
Reverse voltage	V_R	5	V
Forward current	I_F	50	mA
Pulse forward current ^{*1}	I_{FP}	1	A
Power dissipation	P_D	75	mW
Operating temp.	Topr.	- 25 ~ +85	°C
Storage temp.	Tstg.	- 30 ~ +85	°C
Soldering temp. ^{*2}	Tsol.	260	°C

*1. pulse width : $t_w \leq 100 \mu\text{sec.}$ period : $T = 10\text{msec.}$

*2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

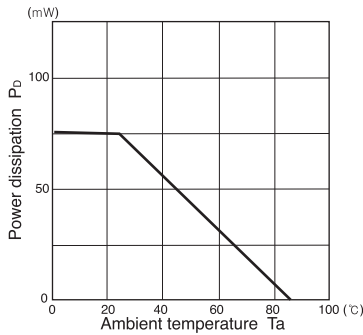
($T_a = 25^\circ\text{C}$)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V_f	$I_f = 50\text{mA}$		1.3	1.5	V
Reverse current	I_R	$V_R = 5\text{V}$			10	μA
Capacitance	C_t	$f = 1\text{MHz}$		25		pF
Radiant intensity	P_o	$I_f = 20\text{mA}$	0.7	2.0		mW/sr
Peak emission wavelength	λ_p	$I_f = 20\text{mA}$		940		nm
Spectral bandwidth 50%	$\Delta \lambda$	$I_f = 20\text{mA}$		50		nm
Half angle	$\Delta \theta$		-	-	-	deg.

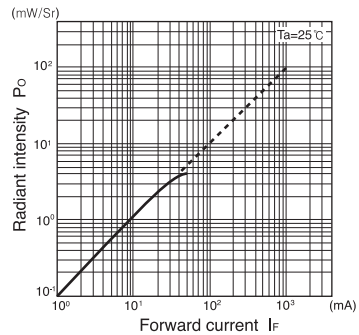
Infrared Emitting Diodes(GaAs)

KEL55L

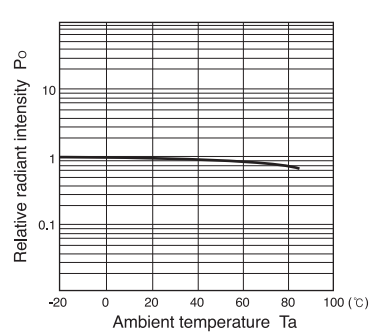
Power dissipation Vs. Ambient temperature



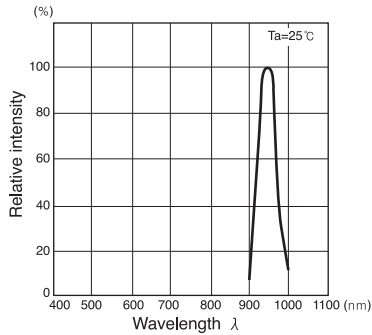
Radiant intensity Vs. Forward current



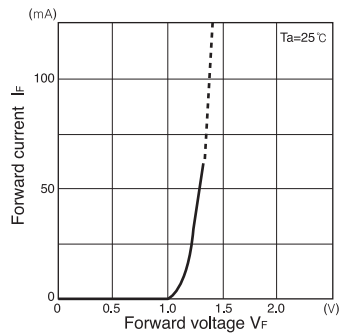
Relative radiant intensity Vs. Ambient temperature



Relative intensity Vs. Wavelength



Forward current vs. Forward voltage



Radiant Pattern

